



GUJARAT TECHNOLOGICAL UNIVERSITY

Programme Name: Master of Engineering

Level: PG

Subject Code : ME02000151

Subject Name : VLSI Fabrication Technology

WEF Academic Year :	2024-25
Semester :	2
Category of the Course :	PCC-03 / PEC-04

Course Outcome :

After Completion of the Course, Student will able to :

No	Course Outcomes	RBT Level*
01	Understand silicon wafer preparation processes.	UN
02	Learn the different process steps involved in the fabrication of VLSI circuits along with limitations.	UN
03	Appreciate use of process simulator in fabrication of VLSI Circuits.	AP
04	Understand different packaging techniques and related issues.	UN
05	Analyse yield and reliability issues in VLSI.	AN

*RM: Remember, UN: Understand, AP: Apply, AN: Analyze, EL: Evaluate, CR: Create

Prerequisite :	VLSI fabrication technology, manufacturing of VLSI devices, Basics of semiconductor physics
Rationale :	Students of ME in VLSI must possess a good understanding of VLSI fabrication process. Students must learn in detail about various processing steps utilized in fabrication of VLSI IC. As well student should possess knowledge of various analytical and assembly techniques. Student should be familiar with yield and reliability issue in VLSI.

Teaching and Examination Scheme :

Teaching Scheme			Total Credits	Assessment Pattern and Marks				Total Marks
L	T	PR	C	Theory		Practical		
				ESE (E)	PA(M)	ESE (V)	PA (I)	
4	0	0	4	70	30	0	0	100



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Course Content :

Sr. No.	Course Content	No. of Hours	% of Weightage
1	Crystal Growth, Wafer Preparation, Epitaxy and Oxidation : Electronic Grade Silicon, Czochralski crystal growing, Silicon Shaping, processing considerations and future trends, Vapor phase Epitaxy, Molecular Beam Epitaxy, Silicon on Insulators, Epitaxial Evaluation and future trends, Growth Mechanism and kinetics, Thin Oxides, Oxidation Techniques and Systems, Oxide properties, Redistribution of Dopants at interface, Oxidation of Poly Silicon, Oxidation induced Defects.	10	22
2	Lithography and Relative Plasma Etching : Optical Lithography, Electron Lithography, X-Ray Lithography, Ion Lithography, Plasma properties, Feature Size control and Anisotropic Etch mechanism, Reactive Plasma Etching techniques and Equipment, Specific etch processes and future trends.	10	22
3	Deposition, Diffusion, Ion Implementation and Metallization : Deposition process, Poly silicon, plasma assisted Deposition, Models of Diffusion in Solids, Fick's one dimensional Diffusion Equations, Atomic Diffusion Mechanism, Measurement techniques, Range theory, Implant equipment. Annealing Shallow junctions, High-energy implantation, Physical vapor deposition, Patterning and future trends.	12	22
4	Process Simulation and VLSI Process Integration : Ion implantation, Diffusion and oxidation, Epitaxy, Lithography, Etching and Deposition, NMOS IC Technology, CMOS IC Technology, MOS Memory IC technology, Bipolar IC Technology, IC Fabrication and future trends.	10	22
5	Yield and Reliability Analysis : Mechanisms and modelling of Yield loss in VLSI, Reliability requirement in VLSI, Failure distributions, accelerated testing, Failure mechanisms.	5	12
	Total	47	100

Reference Book :

1. S. M. Sze, "VLSI Technology", McGraw Hill Second Edition. 1998.
2. S.K. Ghandhi, VLSI Fabrication Principles, John Wiley Inc., New York, 1983
3. James D Plummer, Michael D. Deal, Peter B. Griffin, "Silicon VLSI Technology: Fundamentals Practice and Modeling", Prentice Hall India.2000.



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4. Wai Kai Chen, “VLSI Technology” CRC Press, 2003.

List of Laboratory/Learning Resources Required :

1. www.nptel.ac.in
2. www.ocw.mit.edu
3. www.mosis.com
4. www.berkeley.edu

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